MJE350

Plastic Medium Power PNP Silicon Transistor

This device is designed for use in line-operated applications such as low power, line-operated series pass and switching regulators requiring PNP capability.

Features

• High Collector-Emitter Sustaining Voltage -

 $V_{CEO(sus)} = 300 \text{ Vdc} @ I_C$

= 1.0 mAdc

• Excellent DC Current Gain -

 $h_{FE} = 30-240 @ I_C$ = 50 mAdc

- Plastic Thermopad Package
- Pb-Free Package is Available*

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--|-----------------------------------|-------------|------------|
| Collector–Emitter Voltage | V _{CEO} | 300 | Vdc |
| Emitter-Base Voltage | V _{EB} | 3.0 | Vdc |
| Collector Current – Continuous | Ic | 500 | mAdc |
| Total Power Dissipation @ T _C = 25°C Derate above 25°C | P _D | 20 0.16 | W mW/°C |
| Operating and Storage Junction Temperature Range | T _J , T _{stg} | -65 to +150 | °C |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|--------------------------------------|-------------------|------|------|
| Thermal Resistance, Junction-to-Case | $\theta_{\sf JC}$ | 6.25 | °C/W |

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

| Characteristic | Symbol | Min | Max | Unit |
|--|-----------------------|-----|-----|------|
| OFF CHARACTERISTICS | | | | |
| Collector–Emitter Sustaining Voltage ($I_C = 1.0 \text{ mAdc}, I_B = 0$) | V _{CEO(sus)} | 300 | - | Vdc |
| Collector Cutoff Current $(V_{CB} = 300 \text{ Vdc}, I_E = 0)$ | I _{CBO} | - | 100 | μAdc |
| Emitter Cutoff Current ($V_{EB} = 3.0 \text{ Vdc}, I_{C} = 0$) | I _{EBO} | - | 100 | μAdc |
| ON CHARACTERISTICS | | | | |
| DC Current Gain (I _C = 50 mAdc, V _{CE} = 10 Vdc) | h _{FE} | 30 | 240 | - |

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



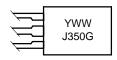
ON Semiconductor®

http://onsemi.com

0.5 AMPERE
POWER TRANSISTOR
PNP SILICON
300 VOLTS, 20 WATTS



MARKING DIAGRAM



Y = Year WW = Work Week J350 = Device Code G = Pb-Free Package

ORDERING INFORMATION

| Device | Package | Shipping |
|---------|---------------------|---------------|
| MJE350 | TO-225 | 500 Units/Box |
| MJE350G | TO-225 (Pb-Free) | 500 Units/Box |

MJE350

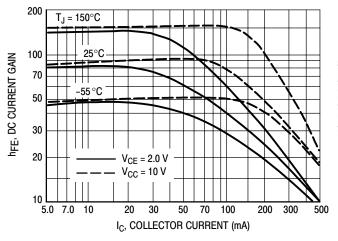


Figure 1. DC Current Gain

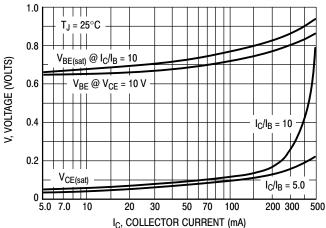


Figure 2. "On" Voltages

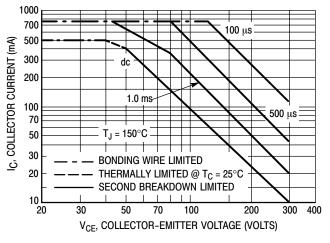


Figure 3. Active-Region Safe Operating Area

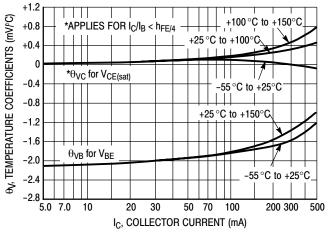


Figure 4. Temperature Coefficients

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 3 is based on $T_{J(pk)} = 150^{\circ} C$; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^{\circ} C$. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

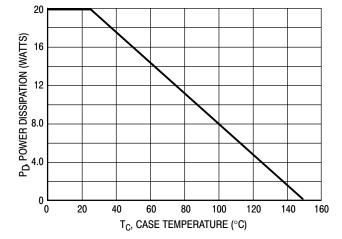
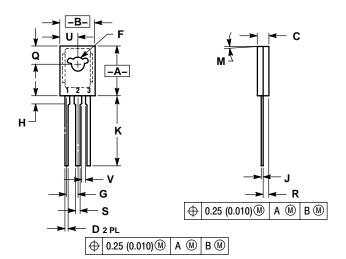


Figure 5. Power Derating

MJE350

PACKAGE DIMENSIONS

TO-225 CASE 77-09 ISSUE Z



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
 - CONTROLLING DIMENSION: INCH.
- 3. 077-01 THRU -08 OBSOLETE, NEW STANDARD 077-09.

| | INCHES | | MILLIMETERS | | |
|-----|--------|-------|-------------|-------|--|
| DIM | MIN | MAX | MIN | MAX | |
| Α | 0.425 | 0.435 | 10.80 | 11.04 | |
| В | 0.295 | 0.305 | 7.50 | 7.74 | |
| С | 0.095 | 0.105 | 2.42 | 2.66 | |
| D | 0.020 | 0.026 | 0.51 | 0.66 | |
| F | 0.115 | 0.130 | 2.93 | 3.30 | |
| G | 0.094 | BSC | 2.39 BSC | | |
| Н | 0.050 | 0.095 | 1.27 | 2.41 | |
| J | 0.015 | 0.025 | 0.39 | 0.63 | |
| K | 0.575 | 0.655 | 14.61 | 16.63 | |
| M | 5° | TYP | 5° | TYP | |
| Q | 0.148 | 0.158 | 3.76 | 4.01 | |
| R | 0.045 | 0.065 | 1.15 | 1.65 | |
| S | 0.025 | 0.035 | 0.64 | 0.88 | |
| U | 0.145 | 0.155 | 3.69 | 3.93 | |
| ٧ | 0.040 | | 1.02 | | |

STYLE 1:

PIN 1. EMITTER

2. COLLECTOR

3 BASE

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